

ABSTRACT

[0029] Disclosed herein is a method of forming a metal line of a semiconductor device. The method includes forming a metal line connected to an underlying element by, for example, performing a main etching process and an over-etching process, at the same time, forming a metal fuse of which one side is connected to the metal line and the other side is connected to a semiconductor substrate. The method also includes forming the metal line of the semiconductor device by, for example, performing an over-etching process for isolating the metal line and the metal fuse electrically. Charges induced by plasma during the over-etching process for forming the metal line are accumulated in the metal line. According to the present invention, it is possible to minimize damage on the underlying element, since plasma-induced charges accumulated in the metal line are discharged into the semiconductor substrate through the metal fuse.